

CMSSH-3
CMSSH-3A
CMSSH-3C
CMSSH-3S
SURFACE MOUNT
SUPERmini™
SILICON SCHOTTKY DIODES

SUPERmini™



SOT-323 CASE

Central™

Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMSSH-3 Series types are Silicon Schottky Diodes, epoxy molded in a SUPERmini™ surface mount package, designed for fast switching applications requiring a low forward voltage drop.

CMSSH-3: SINGLE
 CMSSH-3A: DUAL, COMMON ANODE
 CMSSH-3C: DUAL, COMMON CATHODE
 CMSSH-3S: DUAL, IN SERIES

MARKING CODE: 95D
MARKING CODE: B1D
MARKING CODE: B2D
MARKING CODE: A5D

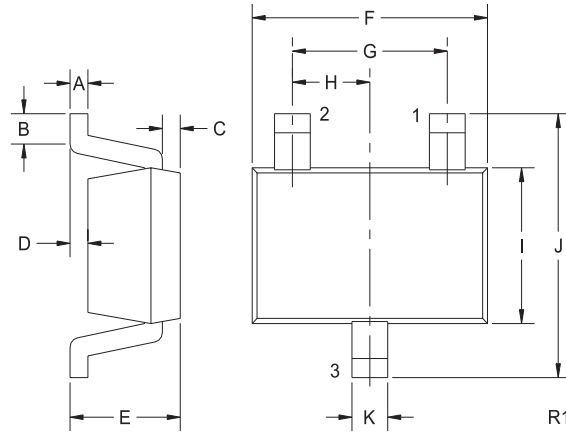
MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

	SYMBOL		UNITS
Peak Repetitive Reverse Voltage	V_{RRM}	30	V
Continuous Forward Current	I_F	100	mA
Peak Repetitive Forward Voltage	I_{FRM}	350	mA
Forward Surge Current, $t_p=10\text{ms}$	I_{FSM}	750	mA
Power Dissipation	P_D	250	mW
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
Thermal Resistance	Θ_{JA}	500	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS PER DIODE: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
B_{VR}	$I_R=100\mu\text{A}$	30			V
V_F	$I_F=2.0\text{mA}$		0.29	0.33	V
V_F	$I_F=15\text{mA}$		0.40	0.45	V
V_F	$I_F=100\text{mA}$		0.74	1.00	V
I_R	$V_R=25\text{V}$		90	500	nA
I_R	$V_R=25\text{V}, T_A=100^\circ\text{C}$		25	100	μA
C_T	$V_R=1.0\text{V}, f=1\text{ MHz}$		7.0		pF
t_{rr}	$I_F=I_R=10\text{mA}, I_{rr}=1.0\text{mA}, R_L=100\Omega$			5.0	ns

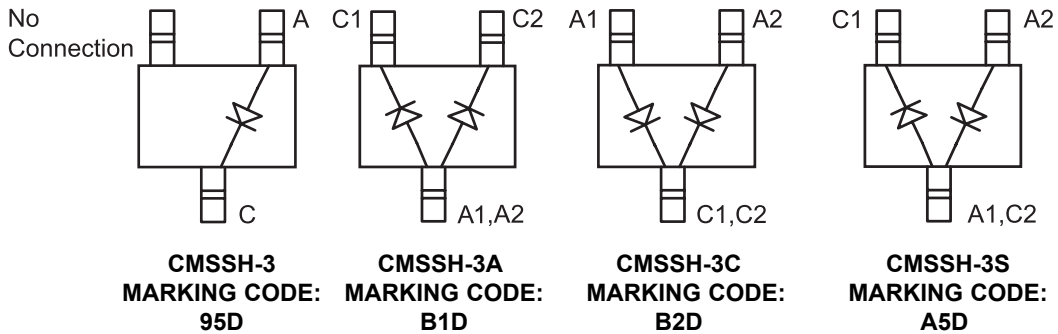
SOT-323 CASE - MECHANICAL OUTLINE



SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.008	0.10	0.20
B	0.004	-	0.10	-
C	0.004	0.008	0.10	0.20
D	-	0.004	-	0.10
E	0.031	0.043	0.80	1.10
F	0.071	0.087	1.80	2.20
G	0.051		1.30	
H	0.026		0.65	
I	0.045	0.053	1.15	1.35
J	0.079	0.087	2.00	2.20
K	0.008	0.016	0.20	0.40

SOT-323 (REV: R1)

PIN CONFIGURATION



R1 (13-November 2002)